

35.C13630



PATENT APPLICATION

Receipt
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
: Examiner: N/Y/A
MASAAKI IWANE ET AL.)
: Group Art Unit: 2815
Appln. No.: 09/346,678)
:
Filed: July 2, 1999)
:
For: CRYSTAL GROWTH PROCESS,)
SEMICONDUCTOR DEVICE,)
AND ITS PRODUCTION)
PROCESS : April 24, 2000

Assistant Commissioner for Patents
Washington, D.C. 20231

SECOND REQUEST FOR CORRECTED FILING RECEIPT

Sir:

Applicants' attorney has received an Corrected Filing Receipt in the above-identified application in which the following inaccuracy is still noted:

The foreign applications data is still incorrect and should read as follows:

--JAPAN 10-202887 FILED JULY 3, 1998


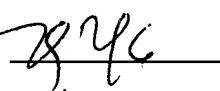
JAPAN 11-188466 FILED JULY 2, 1999--.

Issuance of a corrected Filing Receipt with the above noted correction is respectfully requested.

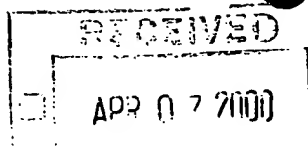
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MAY 10 2000
TECHNOLOGY CENTER 2800

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our below listed address.

Respectfully submitted,


Attorney for Applicants
Registration No. 

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CORRECTED FILING RECEIPT



OC00000005014053



UNITED STATES DEPARTMENT OF COMMERCE
Patent and Trademark Office

Address: ASSISTANT SECRETARY AND
COMMISSIONER OF PATENT AND TRADEMARKS
Washington, D.C. 20231

APPLICATION NUMBER	FILING DATE	GRP ART UNIT	FIL FEE REC'D	ATTY. DOCKET NO	DRAWINGS	TOT CLAIMS	IND CLAIMS
09/346,678	07/02/1999	2815	890	35.C13630	9	9	3

ASH

FITZPATRICK CELLA HARPER & SCINTO
30 ROCKEFELLER PLAZA
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corr. fil. RPT.

Date Mailed: 03/28/2000

Receipt is acknowledged of this nonprovisional Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. **If an error is noted on this Filing Receipt, please write to the Office of Initial Patent Examination's Customer Service Center. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the PTO processes the reply to the Notice, the PTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).**

Applicant(s)

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Continuing Data as Claimed by Applicant

Foreign Applications

JAPAN 10-202887 03/07/1998
JAPAN 11-188466 02/07/1999

If Required, Foreign Filing License Granted 08/03/1999

Title

CRYSTAL GROWTH PROCESS, SEMICONDUCTOR DEVICE, AND ITS PRODUCTION PROCESS

Preliminary Class

257

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Bib Data Sheet


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 Address: COMMISSIONER OF PATENTS AND TRADEMARKS
 Washington, D.C. 20231

SERIAL NUMBER 09/346,678	FILING DATE 07/02/1999 RULE -	CLASS 257	GROUP ART UNIT 2815	ATTORNEY DOCKET NO. 35.C13630
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APPLICANTS
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**** CONTINUING DATA *******

**** FOREIGN APPLICATIONS *******
 JAPAN 10-202887 07/03/1998 ✓
 JAPAN 11-188466 07/02/1999 ✓

IF REQUIRED, FOREIGN FILING LICENSE GRANTED **
 ** 08/03/1999

Foreign Priority claimed <input checked="" type="checkbox"/> yes <input type="checkbox"/> no	STATE OR COUNTRY JAPAN	SHEETS DRAWING 9	TOTAL CLAIMS 9	INDEPENDENT CLAIMS 3
35 USC 119 (a-d) conditions met <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance				
Verified and Acknowledged Examiner's Signature: [Signature] Initials: [Initials]				

ADDRESS
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TITLE
CRYSTAL GROWTH PROCESS, SEMICONDUCTOR DEVICE, AND ITS PRODUCTION PROCESS

FILING FEE RECEIVED 890	FEES: Authority has been given in Paper No. _____ to charge/credit DEPOSIT ACCOUNT No. _____ for following:	<input type="checkbox"/> All Fees
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		<input type="checkbox"/> 1.18 Fees (Issue)
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